Calculation of the Band Structure and Optical Constants of Diamond Using the Nonlocal-Pseudopotential Method

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The electronic band structure and optical constants of diamond are calculated using the empirical-pseudopotential method with an additional ε-1 nonlocal term $V_{NL}(r)$ added to account for the strong potential experienced by $p$ electrons in the core region. $V_{NL}(r)$ strongly affects the $p$-like conduction bands, and the resulting band structure yields a plot of $\epsilon_2(\omega)$, the imaginary part of the dielectric function, which is in satisfactory agreement with experiment. In addition, the temperature-dependent peak at 7.8 eV in the optical spectrum, whose origin has been somewhat of a mystery, is identified with optical transitions beginning at $L$ and extending out along the $\bar{A}$ direction in the Brillouin zone.

INTRODUCTION

The band structure of diamond has been extensively studied by several authors\textsuperscript{1-3} in recent years. We will focus here on those calculations utilizing the empirical-pseudopotential method\textsuperscript{1-3} (EPM) with the aim of extending these calculations. Since good pseudopotential calculations for silicon are presently available in the literature,\textsuperscript{6} it would seem to be possible to combine the best sets of form factors for C and Si to determine a consistent band structure for SiC. Furthermore, the form factors for C can be used to determine the symmetric part of the form factors for BN and BP. However, before proceeding directly toward these goals, further improvement on the presently available diamond calculations is considered necessary as the resulting band structures do not yield a totally satisfactory fit to the experimental optical data. In particular, the calculated $\epsilon_2$ spectra of
diamond do not match the measured spectra very well, especially with respect to the line shape in the low-energy region and the position of the main peak.

In an attempt to correct for the above deficiencies, we present in this paper another calculation of the band structure and optical properties of diamond. However, instead of making the usual assumption that the pseudopotential can be approximated by a local spherically symmetric potential which is independent of the angular momentum of the state under consideration, we have included a nonlocal term \( V_{NL}(\mathbf{r}) \) to account for the angular-momentum dependence of the pseudopotential. Such a term does indeed lead to an improved line shape in the low-energy region and yields a main peak whose position is in excellent agreement with experiment. In addition, the band structure thus obtained suggests a new interpretation of some of the optical structure. We shall describe more fully, in what follows, the details and results of these calculations. The paper will be presented in three sections. In Sec. I we discuss the choice of \( V_{NL}(\mathbf{r}) \), and the mechanics of the calculation are briefly described; in Sec. II the resulting energy-band structure and optical parameters are discussed and compared with the results of other authors; finally, in the final section conclusions drawn from the calculation are presented.

I. NONLOCAL ANALYSIS

In the original formulation of the pseudopotential method, as described by Phillips and Kleinman, instead of solving the one-electron Schrödinger equation for a periodic crystal

\[
[\left(\frac{\hbar^2}{2m}\right) + V_{F}(\mathbf{r})] \phi_{n}(\mathbf{r}) = E_{n}(\mathbf{k}) \phi_{n}(\mathbf{r}) ,
\]

where \( p \) and \( m \) are the momentum and mass of the electron and \( V_{F}(\mathbf{r}) \) is the crystal potential, one considers instead the following model equation for a smoothed pseudo-wave-function \( \phi_{n}(\mathbf{r}) \),

\[
[\left(\frac{\hbar^2}{2m}\right) + V_{p}(\mathbf{r})] \phi_{n}(\mathbf{r}) = E_{n}(\mathbf{k}) \phi_{n}(\mathbf{r}) ,
\]

where \( V_{p} \) is a nonlocal integral operator representing the sum of the usual attractive Coulomb crystal \( V_{C} \) and a nonlocal angular-momentum-dependent repulsive potential \( V_{R} \), which arises from the orthogonality of the true wave functions to the core states.

In order to solve Eq. (2), the usual procedure is to assume the cancellation between \( V_{R} \) and \( V_{C} \) to be almost complete, and to replace \( V_{p} \) by a weak potential which is independent of angular momentum. In addition, one generally approximates the pseudopotential by a local spherically symmetric potential, which is assumed to be expressible as a superposition of local spherically symmetric potentials centered about each ion site. With these approximations, one can then write

\[
V_{p}(\mathbf{r}) = \sum_{j} v(|\mathbf{r} - \mathbf{R}_{j}|) ,
\]

where \( v(|\mathbf{r} - \mathbf{R}_{j}|) \) is the local potential centered at \( \mathbf{R}_{j} \), the position of the \( j \)th ion core, and the sum is over all the ion cores in the crystal. The problem of determining the energy eigenvalues and pseudo wave functions is thus reduced to solving the somewhat simpler equation

\[
[\left(\frac{\hbar^2}{2m}\right) + \sum_{j} v(|\mathbf{r} - \mathbf{R}_{j}|)]\phi_{n}(\mathbf{r}) = E_{n}(\mathbf{k})\phi_{n}(\mathbf{r})
\]

for the various cases of interest.

It is from this point that previous EPM calculations have proceeded. However, in the case of diamond the agreement between the results of such calculations and the experimental optical data is not particularly good. This is somewhat surprising, since Eq. (4) leads to good results for Ge and Si, which have essentially the same structure. This suggests that the approximations leading to Eq. (4) should be reexamined for diamond. In particular, the approximation involved in ignoring the angular momentum dependence of \( V_{p} \) seems somewhat questionable. Unlike Si and Ge, diamond has no \( p \) electrons in the core; hence, the Coulomb potential felt by the \( p \) valence and conduction electrons is not canceled in the core region by a repulsive term from \( V_{R} \). As a result, Phillips's cancellation theorem is not valid in this case, and one cannot assume \( V_{p} \) to be weak in this region for such electrons. In light of this fact, we modify Eq. (4) in our calculation by adding to it a nonlocal term \( V_{NL}(\mathbf{r}) \) to account for the strong potential experienced by \( p \) states in the core region. Thus, instead of using Eq. (4) as a starting point for our calculation we use the following equation:

\[
[\left(\frac{\hbar^2}{2m}\right) + \sum_{j} v(|\mathbf{r} - \mathbf{R}_{j}|)]

V_{NL}(\mathbf{r})\phi_{n}(\mathbf{r}) = E_{n}(\mathbf{k})\phi_{n}(\mathbf{r}) ,
\]

where \( V_{NL}(\mathbf{r}) \) is assumed to operate only on \( p \) states in the core region. To satisfy these conditions, we have followed the analysis of Lee and Falicov for F and the analysis of Kong and Cohen in their treatment of KCl by choosing \( V_{NL}(\mathbf{r}) \) to have the form

\[
V_{NL}(\mathbf{r}) = \sum_{j} P_{l}^{*}v(|\mathbf{r} - \mathbf{R}_{j}|)P_{l} ,
\]

where \( P_{l} \) is a projection operator which operates only on those spherical harmonics with \( l = 1 \), and \( P_{l}^{*} \) is the corresponding Hermitian conjugate operator.

During the course of the calculation, several
forms of $U(|\mathbf{r}|)$ were tried, such as a simple square well, a Yukawa-type well, etc. The best results are obtained by choosing

$$U(|\mathbf{r}|) = \begin{cases} A e^{-\alpha r}, & r \leq R_s \\ 0, & r > R_s \end{cases}$$

(7)

where $R_s$ is the diamond core radius in the crystal, assumed to retain its free-atom value of approximately 0.2 Å, and $\alpha$ and $R_s$ are treated as parameters. This choice of $U(|\mathbf{r}|)$ is vaguely suggestive of the Coulomb potential (proportional to $1/r$) felt by an atomic $p$ electron which has an associated radial charge density of the form $r^2 e^{-\alpha r}$ in the presence of a point nucleus. The calculation resulting from this choice of $U$ will be the only one discussed in this paper.

To solve (5), it is convenient to expand the weak local-pseudopotential term in the reciprocal lattice as follows:

$$\sum_{\mathbf{G}} v(|\mathbf{r} - \mathbf{G}|) = \sum_{\mathbf{G} \in \mathbf{G}_1} v(|\mathbf{G}|) S(|\mathbf{G}|) e^{i \mathbf{G} \cdot \mathbf{r}}$$

(8)

where $\mathbf{G}$ is a reciprocal-lattice vector in units of $2\pi/a$, $a$ being the lattice constant of diamond taken to be the value 3.57 Å, and where

$$v(|\mathbf{G}|) = \frac{2}{\Omega} \int_{\text{cell}} v(|\mathbf{r}|) e^{-i \mathbf{G} \cdot \mathbf{r}} d^3 r$$

(9)

is the crystal form factor, $\Omega$ being the volume of the unit cell, and

$$S(|\mathbf{G}|) = \cos \mathbf{G} \cdot \mathbf{r}$$

(10)

is the structure factor, $\mathbf{r} = \frac{1}{2} a (1,1,1)$ being the vector between the two diamond atoms in the unit cell. With the truncation of the expansion at $|\mathbf{G}|^2 = 12$ in (8), the only nonvanishing form factors are $v(|\mathbf{G}|^2 = 3), v(4), v(8), v(11)$, and $v(12)$. $v(4)$ and $v(12)$ do not contribute to the potential because the corresponding structure factors $S(4)$ and $S(12)$ are 0. However, we set $S(12) = 1$ in order to be consistent with the x-ray scattering data.\(^{11,12}\)

Having made the expansion (8), one then diagonalizes the pseudopotential Hamiltonian (5) over a basis of plane-wave states. The matrix elements for the local pseudopotential are calculated by a method described by Brust.\(^{13}\) Essentially, this method consists of treating those plane waves satisfying $|\mathbf{k} + \mathbf{G}|^2 \leq E_1$ exactly, while those with $E_1 < |\mathbf{k} + \mathbf{G}|^2 \leq E_2$ enter only through second-order perturbation theory. Plane waves with $|\mathbf{k} + \mathbf{G}|^2 > E_2$ are neglected. For the nonlocal term $V_{NL}(|\mathbf{r}|)$ we also neglect the contributions of those plane waves with $E_1 < |\mathbf{k} + \mathbf{G}|^2 \leq E_2$. A typical matrix element of $V_{NL}$ is of the form

$$\langle \mathbf{k} + \mathbf{G} | V_{NL} | \mathbf{k} + \mathbf{G}' \rangle = I_{GG'} (24/\Omega) \cos \theta_{GG'} S(|\mathbf{G} - \mathbf{G}'|)$$

(11)

where $I_{GG'} = \int j_j(|\mathbf{k} + \mathbf{G}| r) j_j(|\mathbf{k} + \mathbf{G}'| r) U(r)r^2 dr$\(^\text{12}\)

and where $j_j$ is the spherical Bessel function of order $j$, $\phi_{GG'}$ is the angle between the vectors $\mathbf{k} + \mathbf{G}$ and $\mathbf{k} + \mathbf{G}'$, and $G$ and $S$ are the volume of the unit cell and structure factor as defined previously. The integral is evaluated numerically. Satisfactory convergence is obtained by choosing $E_1 = 12.50$ and $E_2 = 30.10$.

The EPM method of solution of (5) consists in choosing the pseudopotential form factors $v(|\mathbf{G}|)$, along with the parameters $A$, $\alpha$ associated with $U(|\mathbf{r}|)$, to give band structures consistent with experiment. In practice, one calculates a few of the principal band gaps at important symmetry points in the Brillouin zone, and then adjusts these parameters until the gap values agree with those extrapolated from the optical experimental data. Once these parameters are fixed, the energies can be calculated at general points throughout the zone. The resulting band structure and pseudo-wave-functions can then be used to calculate $\varepsilon_2$ via the expression

$$\varepsilon_2(\omega) = \frac{e^2 \hbar^2}{m} \sum_{\nu, \nu'} \frac{2}{(2\pi)^3} \int_{E_{\nu - \nu'}} \frac{\text{d}S}{E_{\nu - \nu'}^{1/2}}$$

(13)

where

$$f_{\nu, \nu'}(\mathbf{K}) = \frac{2}{3m} \frac{|\langle \mathbf{k}, \nu | \mathbf{r} | \mathbf{k'}, \nu' \rangle|^2}{E_{\nu - \nu'}}$$

is the EPM interband oscillator strength, $|\mathbf{k}, \nu \rangle$ and $|\mathbf{k'}, \nu' \rangle$ are the EPM wave functions for the conduction and valence bands at the point $\mathbf{k}$, $S$ is a surface of constant interband energy $E_{\nu - \nu'} = E_{\nu} - E_{\nu'}$, and $E_{\nu}$ and $E_{\nu'}$ are the energies of the conduction and valence bands, respectively. The details of evaluating the sums over initial and final states is described elsewhere.\(^{14}\) The only modifications are that the mesh size is defined by dividing the distance $kX$ into 10 parts, and each cube is divided into 125 equal subcubes yielding $\sim 13 500$ random points, and quadratic interpolation between mesh points in used instead of linear interpolation. The whole process is repeated until satisfactory agreement with the optical data is obtained or until no further improvement can be obtained.

The available optical data for diamond can be summarized by a plot of $\varepsilon_2$,\(^{15}\) as shown by the dashed line in Fig. 2. We also list the measured values of the conduction-band minimum $\Delta_{\text{min}}$ and the threshold for indirect transitions $E_{\text{ind}}$,\(^{16,17}\) (see Table II). As can be seen, the experimental $\varepsilon_2$ has structure at 7.2, 7.8, 12, and 16 eV. Presumably, these structures can be related to Van Hove singularities at critical points, where $\nu_{2} E_{\text{vc}} = 0$, although it is possible that they may also arise from transitions extending over large regions of $k$ space around symmetry points, as Kane showed to be the case for Si.\(^{18}\) It is by identifying the
structure with transitions at certain critical symmetry points that one determines the data to which the form factors are fitted.

Unfortunately, no clear-cut interpretations of the critical points causing the principal structure in the low-energy region of the diamond $\varepsilon_2$ spectrum exist. The shoulder at 7.2 eV is temperature independent, which suggests that the threshold for direct transitions is near this energy. However, there is some debate as to whether this fundamental absorption edge begins with transitions at $\Gamma$ or $L$. The peak at 7.8 eV is temperature dependent, which suggests the possibility of its being caused by an exciton; however, previous calculations yield no critical point near this energy with which such an exciton can be associated.

By contrast, the origin of the main peak at 12 eV is understood to arise from $4 \rightarrow 5$ transitions starting at $X_4 - X_5$ and extending out along the $\Sigma$ directions where there is a large region of essentially parallel bands. The structure at 16 eV is not sharp and is at too high an energy to be given accurately by our EPM approximation.

For the purposes of this calculation, then, the only unambiguous experimental data to which the form factors can be fitted are the threshold for indirect transitions, the position of the conduction-band minimum, and the position of the main peak, which is expected to lie near the $X_4 - X_5$ transition energy. The experimental values taken for these quantities are listed in Table II, under experiment. In addition, we assume that the threshold for direct transitions occurs at $\Gamma$ with energy in the vicinity of 7 eV. Since prior calculations agree fairly well with all of the above data except the position of the main peak, we have directed our efforts towards improving this value. As a starting point in our calculation, we use the local form factors $V_{111}$, $V_{220}$, $V_{311}$, $V_{222}$ of Saslow et al. (Table I). They are combined with $A$, $\alpha$ and adjusted until satisfactory agreement with the optical data is reached.

II. DISCUSSION OF RESULTS

The resulting pseudopotential form factors, principal energy gaps, and positions of $\Delta_{\text{bias}}$ and the main peak are given in Tables I and II. For convenience, results of other recent calculations are also listed. The calculated energy-band structure along principal symmetry lines is shown in Fig. 1. Figure 2 contains the calculated $\varepsilon_2(\omega)$ spectrum for the range 0–20 eV, with the corresponding experimentally derived curve also included for comparison. The theoretical reflectance $R(\omega)$, obtained via a Kramers-Kronig analysis of our calculated $\varepsilon_2$, using the method of Walter and Cohen, is shown in Fig. 3, accompanied by the measured curve. Finally, Figs. 4 and 5 indicate important energy contours and critical points for $4 \rightarrow 5$ and $4 \rightarrow 6$ transitions, respectively.

We will first consider the calculated band structure. The valence-band maximum is at $\Gamma$, and the conduction-band minimum occurs near (0, 0, 0), which is in good agreement with the value of (0.78 ± 0.02, 0, 0) obtained via neutron diffraction studies. The threshold for indirect transitions is seen to be 5.46 eV, in excellent agreement with experiment. The threshold for direct transitions is 6.96 eV, and corresponds to $\Gamma_{\mu} \rightarrow \Gamma_{\mu'}$ transitions. The band structure is similar in most respects to those of prior calculations, including the APW calculations of Kohn and Herman's OPW calculation. However, there are some significant differences, mainly with respect to the level ordering at $\Gamma$ and $L$. The present calculation has $\Gamma_{\mu}$ lower than $\Gamma_{15}$, which agrees with Saravia and Brust, but is opposite to the ordering of other calculations. A priori, there is no reason for choosing one ordering over the other. One might argue that since Ge and Sn have $\Gamma_{\mu}$ lower than $\Gamma_{15}$, while Si has the order reversed, C could be expected to follow the trend and have $\Gamma_{15}$ lower in energy than $\Gamma_{\mu}$. However, there are no experimental data presently available which favor one ordering over the other. Until such time as experiments can isolate some effect which differentiates between the two, the question of which ordering is correct remains open. Another difference in the levels occurs at $L$, where $L_{\mu}$ is lower in energy than $L_1$, $L_2$, and $L_3$, and $L_1$ and $L_2$ are reversed, with $L_3$ lower than $L_1$. The fact that $L_{\mu}$ lies lower than $L_1$, $L_2$ is related to the fact that $\Gamma_{\mu}$ lies below $\Gamma_{15}$. The peak which appears at 8.4 eV in the calculated reflectance spectrum (Fig. 3) is a consequence of the fact that the conduction band at $L(L_{\mu})$ has been brought down closer to the valence band.

The calculated $\varepsilon_2$ spectrum begins with direct $4 \rightarrow 5$ transitions at $\Gamma$ with energy 6.96 eV. As just discussed, this corresponds to the $\Gamma_{\mu} \rightarrow \Gamma_{15}$ transition, which has $M_5$ symmetry. Since the contributions to $\varepsilon_2$ near 7 eV come from a very small region in $k$ space, as shown in Fig. 4, the absorption edge is very weak in this vicinity and does not show up well on the curve. As the energy is increased, more and more states are able to contribute, and $\varepsilon_2$ starts to rise. The slope in the region 7.5–8 eV is quite steep because the joint density of states with transition energies in this range increases quite rapidly, as indicated by the much larger energy contour for 8.1 eV in Fig. 4(a), and the associated oscillator strengths are very large, especially out along the $\Lambda$ and $\Sigma$ directions from $\Gamma$. At 8 eV the curve starts to
level off somewhat, as the increase in \( J_{\text{sc}} \), the joint density of states, is not quite as rapid as before; in addition, much of the increase in \( J_{\text{sc}} \) comes from interior points in the zone in a region where the oscillator strengths are generally weaker than before.

Near 8.2 eV, \( \epsilon_2 \) again changes slope and begins another steep ascent until \( \hbar \omega = 8.4 \) eV, where it starts to level off again. In this region there are three main contributions to \( \epsilon_2 \). First, there is an \( M_0 \) singularity at \( \Gamma \), corresponding to the 4 - 6 transition \( \Gamma_6' \rightarrow \Gamma_4 \) with energy 8.2 eV. In addition, there is a second critical point at \( L \) which has \( M_1 \) symmetry and is associated with the 4 - 5 transition \( L_4' - L_5' \) of energy 8.27 eV. Finally, there is a large increase in \( J_{\text{sc}} \) in this energy interval coming mostly from 4 - 5 transitions in the region around \( L \) and extending out along \( \Lambda \), where the oscillator strengths are fairly large.

The structure exhibited by \( \epsilon_2 \) from 8.4 to 11.5 eV is not associated with any critical points but seems to be solely due to a volume effect. The major contributions come from 4 - 5 transitions in the interior of the zone, as shown in Fig. 4 for selected energies; 4 - 6 transitions around \( \Gamma \) also contribute, but not significantly, as the available phase space is of limited extent, and the oscillator strengths are generally weaker. The roughness in the region 8.4 - 10 eV arises primarily because of the sampling procedure used in evaluating the sum over initial and final states in (13). In this range, the energies change quite rapidly with position in the Brillouin zone. As a result, the meshes used to divide up the Brillouin zone when performing the sums are probably too coarse to yield accurate energy levels and EPM oscillator strengths at random \( k \) values in this region. Previous experience indicates that dividing the Brillouin zone into a finer mesh should smooth out the curve in this region. This belief is strengthened by the fact that the calculated reflectance (Fig. 3) is absolutely smooth in this range. In the interval

| TABLE I. Nonlocal and local form factors (expressed in Ry) used in the present calculation. Also included are the form factors employed in prior EPM calculations. |
|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|
|                 | Local           |                 |                 |                 | Nonlocal        |                 |
|                 | \( V_{11} \)    | \( V_{22} \)    | \( V_{31} \)    | \( V_{32} \)    | \( A \)         | \( \alpha \)     |
| Present calculation | -0.785         | 0.189          | 0.138          | 0.071          | -0.159         | 1.25          |
| Ref. 1          | -0.811         | 0.337          | 0.132          | 0.041          | \* \* \*         | \* \* \*         |
| Ref. 2          | -0.514         | -0.022         | 0.186          | -0.078         | \* \* \*         | \* \* \*         |
| Ref. 3          | -0.696         | 0.337          | 0.132          | 0              | \* \* \*         | \* \* \*         |

| TABLE II. Prominent interband transitions, indirect-band gap, and positions of the conduction-band minimum and main peak in \( \epsilon_2 \) for recent diamond calculations, including the present one. Experimental values are included when applicable. |
|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|
| \( \Gamma_5' \rightarrow \Gamma_4 \) | \( \Gamma_5' \rightarrow \Gamma_6' \) | \( L_4' \rightarrow L_3' \) | \( L_4' \rightarrow L_3 \) | \( X_4 \rightarrow X_3 \) | \( \Gamma_5' \rightarrow \Delta_{\text{min}} \) | \( \Delta_{\text{min}} \) | \( \epsilon_2 \) Main peak |
| Present Calculation (nonlocal EPM) | 8.22 | 6.96 | 8.27 | 13.13 | 11.79 | 5.46 | 0.80 | 11.8 |
| Ref. 3 (EPM) | 14.06 | 7.32 | 7.39 | 17.2 | 10.43 | 5.37 | 0.83 | \*11.0 |
| Ref. 5 (OPW) | 7.1 | 14 | 20.5 | 12.8 | 11.8 | 5.47 | 0.75 |
| Ref. 1 (EPM) | 7.33 | 12.04 | 10.88 | 12.8 | 12.9 | 5.20 | 0.76 | 12.7 |
| Ref. 2 (EPM) | 8.21 | 12.0 | 13.0 | 12.66 | 5.45 | \*0.8 |
| Ref. 4 (APW) | 5.8 | | | | | | |
| Experiment \( 7-7, 3^{2s}, h^c \) | \( 7-7, 3^{2s}, h^c \) | \*12 | | | 5.47 | 0.78 | 12 |

\*The entry in this slot depends on whether one assigns the direct gap at \( \Gamma \) to the \( \Gamma_5' \rightarrow \Gamma_1 \) or \( \Gamma_5' \rightarrow \Gamma_5' \) transitions.
\*Ref. 16
\*Ref. 18
\*Ref. 17
10–11.5 eV, the major contribution to $\epsilon_2$ comes from 4–5 transitions in the interior of the zone, coming closer to the region around $K$, $U$, $X$ as the energy increases. The steep rise in $\epsilon_2$ is due to the fact that the oscillator strengths become significantly stronger as one goes away from $\Gamma$, $L$ and toward the region around $K$, $U$, $X$.

The large main peak at 11.8 eV is caused by the $M_1$ critical point at $X$ with energy 11.79 eV, corresponding to the 4–5 transition $X_4 \rightarrow X_1$. The main contribution still comes from 4–5 transitions, especially those in the XTKW plane as shown in Fig. 4(b). 3–5 and 4–6 transitions also combine in roughly equal proportions to make up about 10% of the total contribution to $\epsilon_2$ at this point.

As one goes higher in energy, the 4–6 transitions become more and more important. Since the oscillator strengths are generally much weaker than those corresponding to the 4–5 transitions, $\epsilon_2$ falls smoothly as energy increases. The peak at 13.2 eV is due to the $M_1$ critical point at $L$, associated with the 4–6 transition $L_3 \rightarrow L_{31}$, with energy 13.13 eV. The small peak at 14.4 eV is caused by the 4–6 transition $\Delta_5 \rightarrow \Delta_{51}$ at the point (0.5, 0, 0); this transition has energy 14.38 eV and $M_2$ symmetry.

A comparison with the experimentally derived $\epsilon_2$ yields generally adequate agreement (Table III). The main purpose of this calculation is to try to improve the agreement between the position of the main peak in the theoretical and experimental results. In previous calculations, the calculated position of the main peak is displaced from its experimental value by ~1 eV. As seen from Fig. 2, in this calculation the two peaks are in excellent agreement.
agreement, differing in position by only 0.2 eV. The calculated peak is somewhat larger in magnitude but this seems to be characteristic of the EPM-type calculations. The height of the experimental $\epsilon_s$ curve is somewhat arbitrary, anyway, as surface contamination of the sample can lead to differences in peak height of up to 20%\(^{15}\) in the measured reflectance from which $\epsilon_s$ is derived. Since the measured and calculated peak heights for the reflectance differ by only approximately 5%, as shown in Fig. 3, one can assume that the magnitude differences in $\epsilon_s$ are probably due to the different methods employed in evaluating the Kramers-Kronig integrals in the higher-energy regions; we used an analytic tail of the form $\beta \omega/(\omega^2 + \gamma^2)^2$ to replace the calculated $\epsilon_s(\omega)$ for energies above 24 eV, while Walker used Roessler’s method\(^{20}\) to extend his values of $R(\omega)$ beyond the

FIG. 2. Calculated and experimental $\epsilon_s(\omega)$ spectra. The full line represents the calculated results using $V_{Gj}(\bar{r})$, while the experimental curve is denoted by the dashed line.
measured range 5–31 eV. (See Refs. 15 and 19 for more detailed comparison of the methods.) The difference in magnitudes of the two $\varepsilon_2$, along with the different extrapolation methods used, should also explain why the positions of the main peak are displaced further apart in $R(\omega)$ (≈ 0.4 eV) than in $\varepsilon_2$. Any altering of the peak heights in $R(\omega)$ (or $\varepsilon_2$) would be expected to cause energy shifts when transforming to $\varepsilon_2(\omega)$ (or $R$).

The agreement between theory and experiment in the 7–10–eV region is not extremely good, but this range has always been a troublesome one for theorists. As remarked earlier, the cause of the experimental structure between 7–8 eV is very uncertain. The calculated $\varepsilon_2$ starts off with a slope very similar to that of the measured curve, but displaced approximately 0.8 eV higher in energy. The shape of this absorption edge is much improved over that obtained by Saravia and Brust, using Saslow’s form factors, which is much too weak compared to experiment. Saravia and Brust do calculate a strong absorption edge near 7.3 eV with their model II, but the slope is too steep, being almost vertical and essentially forming a step function. Neither calculation accounts for the peak at 7.8 eV. A close look at Fig. 2 shows two "bends" in the calculated $\varepsilon_2$ at 8.1 and 8.3 eV. This structure shows up more prominently in $R(\omega)$ (Fig. 3), where there are two small peaks at 8.3 and 8.6 eV. These seem to correspond to the measured peaks at 7.2 and 7.6 eV, but are displaced in energy by ~1 eV. Since these calculated peaks are caused by the $M_6$ and $M_5$ critical points at $\Gamma$ and $L$, respectively, it seems likely that their positions could be shifted down in energy by reducing the energy gaps between $L_{2\gamma}$ and $L_{2\gamma}$ at $L$. Unfortunately, this turns out to be very difficult with our model potential for $U(r)$. It was found that decreasing the $L_{2\gamma} - L_{2\gamma}$ gap at $L$ could only be accomplished by lowering the conduction band, the valence band remaining essentially unchanged. However, any significant lowering of the conduction band at $L$ has the effect of shifting the conduction band minimum from $\Delta_{min}$ to $L_{2\gamma}$. Thus, any shifting of the gap at $L$ must be done by shifting the valence band upward.

The gap at $\Gamma$, corresponding to the $\Gamma_{2\gamma} - \Gamma_{15}$ transition, can be handled much more easily. However, as long as $L$ is kept near 8.2 eV in energy, the agreement with experiment of the over-all line shape in the low-energy range deteriorates, with the absorption edge becoming weaker as $\Gamma_{15}$ is lowered. This indicates that one must lower both $\Gamma$ and $L$ at the same time, as the slope of the experimental $\varepsilon_2$ curve in the low-energy region seems to depend on the two gaps being close together in energy. At this time, we have not been able to accomplish the raising of the point $L_{2\gamma}$, the valence band at $L$. However, we tentatively associate the peak at 7.2 in the experimental $\varepsilon_2$ with the $M_0$ critical point at $\Gamma$, corresponding to the $\Gamma_{2\gamma} - \Gamma_{15}$ transition, and the peak at 7.8 eV with the $L_{2\gamma} - L_{2\gamma}$ transition at $L$, which has $M_5$ symmetry. This is the first theoretical identification of a critical point associated with the peak at 7.8 eV. The association of the peak at 7.2 eV with the $\Gamma_{2\gamma} - \Gamma_{15}$ transition is not new, but agrees with the identification made by Herman et al. and Saslow et al. However, in our case we do not also assume that $\Gamma_{2\gamma} - \Gamma_{15}$ forms the threshold for direct transitions, but instead delegate this honor to the $\Gamma_{2\gamma} - \Gamma_{2\gamma}$ transition occurring near 7 eV.
FIG. 4. $4 \rightarrow 5$ energy contours and critical points in the (a) $\Gamma LK$ and $\Gamma LUX$ planes and (b) $\Gamma KWX$ plane.

In the region 8.5–10 eV, the calculated $\epsilon_2$ is too strong and too rough. The roughness probably arises from sampling techniques, as discussed previously, and disappears altogether in reflectance (Fig. 3), which is very smooth in this region; the magnitude of the curve is still larger than the experiment in this region. From 10 to 13 eV the two $\epsilon_2$ plots agree quite well, except for the magnitude of the main peak. The slopes of the two curves are quite similar in this region. From 13 eV and

FIG. 5. $4 \rightarrow 6$ energy contours and critical points in the $\Gamma LK$ and $\Gamma LUX$ planes.
TABLE III. Theoretical and experimental $\epsilon_2$ structure and their identifications, including the location in the Brillouin zone, energy, and symmetry of the calculated critical points. The experimental results are those of Roberts and Walker (Ref. 15).

<table>
<thead>
<tr>
<th>Theory</th>
<th>Experiment</th>
<th>Location in zone</th>
<th>Symmetry</th>
<th>CP energy (eV)</th>
</tr>
</thead>
<tbody>
<tr>
<td>8.1</td>
<td>7.2</td>
<td>$\Gamma_{15} \rightarrow \Gamma_{15}$ (0, 0, 0)</td>
<td>$M_0$</td>
<td>8.22</td>
</tr>
<tr>
<td>8.3</td>
<td>7.8</td>
<td>$L'_2 \rightarrow L'_2$ (0.5, 0.5, 0.5)</td>
<td>$M_1$</td>
<td>8.27</td>
</tr>
<tr>
<td>11.8</td>
<td>12.0</td>
<td>$X \rightarrow X_1$ (1, 0, 0)</td>
<td>$M_1$</td>
<td>11.79</td>
</tr>
</tbody>
</table>

upwards, the calculated curve is again larger than experiment, and has peaks at 13.2 and 14.4 eV, which don't show up in the experimental curve.

CONCLUSIONS

As discussed in Sec. II, the nonlocal EPM calculation seems to explain most of the observed structure in the dielectric constant $\epsilon_2(\omega)$ and the reflectance $R(\omega)$ for diamond, at least qualitatively. The calculation indicates that the experimental peaks in $\epsilon_2$ and $R$ near 8 eV can be associated with the $M_1$ critical point at $L$, even though the calculated value of the $L'_2 - L'_2$ energy gap seems to be ~0.5 eV too large; the temperature dependence of the experimental peak could be caused by an exciton associated with this point. The position of the main peak has been brought into excellent agreement with experiment. Calculations done without $V_{NL}(\Gamma)$ indicate that the nonlocal potential has a definite effect on states within the zone as well as on those along symmetry lines. An illustration of this effect is the significant shift introduced in the position of the main peak, which has large contributions from extended regions in $\overline{k}$ space. Further improvement in the quantitative agreement between theory and experiment in the low-energy region seems to be possible if a method can be found for raising the valence bands $L'_2$ at $L$. The question of the proper ordering of the energy bands at $\Gamma$ will have to remain open until further experiments are done.

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2Work supported in part by the National Science Foundation.
6R. Keown, Phys. Rev. 150, 568 (1965); and references therein.